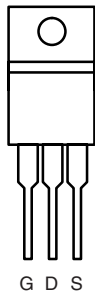


P-Channel 30-V (D-S) 175 °C MOSFET

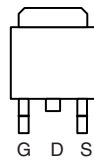
PRODUCT SUMMARY		
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A) ^a
- 30	0.007 at V _{GS} = - 10 V	± 75
	0.010 at V _{GS} = - 4.5 V	± 75


 Available
RoHS*
 COMPLIANT

TO-220AB


Top View

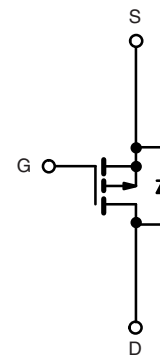
SUP75P03-07

TO-263


Top View

SUB75P03-07

DRAIN connected to TAB



P-Channel MOSFET

Ordering Information: SUB75P03-07 (TO-263)
 SUB75P03-07-E3 (TO-263, Lead (Pb)-free)
 SUP75P03-07 (TO-220AB)
 SUP75P03-07-E3 (TO-220AB, Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS T _C = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Gate-Source Voltage	V _{GS}	± 20	V
Continuous Drain Current (T _J = 175 °C)	I _D	T _C = 25 °C	- 75 ^a
		T _C = 125 °C	- 65
			A
Pulsed Drain Current	I _{DM}	- 240	
Avalanche Current	I _{AR}	- 60	
Repetitive Avalanche Energy ^b	E _{AR}	180	mJ
Power Dissipation	P _D	T _C = 25 °C (TO-220AB and TO-263)	187 ^d
		T _A = 25 °C (TO-263) ^c	3.75
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R _{thJA}	PCB Mount (TO-263) ^c	40
		Free Air (TO-220AB)	62.5
Junction-to-Case	R _{thJC}	0.8	°C/W

Notes:

- Package limited.
- Duty cycle ≤ 1 %.
- When Mounted on 1" square PCB (FR-4 material).
- See SOA curve for voltage derating.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 1		- 3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			- 50	
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			- 250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	- 120			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -30\text{ A}$		0.0055	0.007	Ω
		$V_{GS} = -10\text{ V}, I_D = -30\text{ A}, T_J = 125\text{ }^\circ\text{C}$			0.010	
		$V_{GS} = -10\text{ V}, I_D = -30\text{ A}, T_J = 175\text{ }^\circ\text{C}$			0.013	
		$V_{GS} = -4.5\text{ V}, I_D = -20\text{ A}$		0.008	0.010	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -75\text{ A}$	20			S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1\text{ MHz}$		9000		pF
Output Capacitance	C_{oss}			1565		
Reverse Transfer Capacitance	C_{rss}			715		
Total Gate Charge ^c	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -75\text{ A}$		160	240	nC
Gate-Source Charge ^c	Q_{gs}			32		
Gate-Drain Charge ^c	Q_{gd}			30		
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 0.2\text{ }\Omega$ $I_D \cong -75\text{ A}, V_{GEN} = -10\text{ V}, R_G = 2.5\text{ }\Omega$		25	40	ns
Rise Time ^c	t_r			225	360	
Turn-Off Delay Time ^c	$t_{d(off)}$			150	240	
Fall Time ^c	t_f			210	340	
Source-Drain Diode Ratings and Characteristics ($T_C = 25\text{ }^\circ\text{C}$) ^b						
Continuous Current	I_S				- 75	A
Pulsed Current	I_{SM}				- 240	
Forward Voltage ^a	V_{SD}	$I_F = -75\text{ A}, V_{GS} = 0\text{ V}$		- 1.2	- 1.5	V
Reverse Recovery Time	t_{rr}	$I_F = -75\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		55	100	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			2.5	5	A
Reverse Recovery Charge	Q_{rr}			0.07	0.25	μC

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.